iM1804

P-Channel Enhancement Mode MOSFET

Datasheet

1. Product Information

1.1 Features

- Advanced Trench Cell Design
- Low Thermal Resistance
- RoHS Compliant and Halogen Free



1.2 Package Type

DFN3.3X3.3A-EP1-8L

1.3 Quick Reference

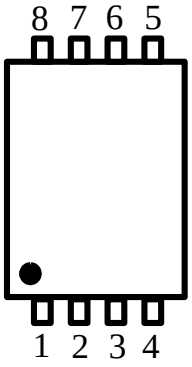
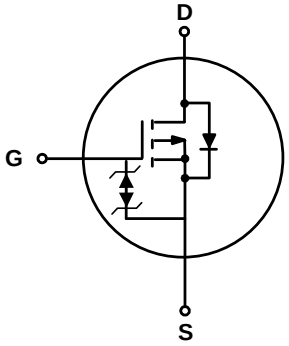
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Limiting Values						
P_{tot}	Total Power Dissipation	T_C = 25 ℃	-	-	41	W
I_{DS}	Drain-Source Current	T_C = 25 ℃, V_{GS} = - 10 V	-	-	- 54	A
		T_C = 100 ℃, V_{GS} = - 10 V	-	-	- 35	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_{DS} = - 250 μA	- 30	-	-	V
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{DS} = V_{GS}, I_{DS} = - 250 μA	- 1	-	- 3	
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS} = - 10 V, I_{DS} = - 11.5 A	-	6	7.5	mΩ
		V_{GS} = - 4.5 V, I_{DS} = - 8.5 A	-	9	11.5	

2. Ordering Code & Marking Information

Ordering Code	Marking Information
iM1804	iM1804 XXXXX X : Date Code

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3. Pin Description

Pin	Description	Simplified Outline	Symbol
1~3	Source (S)		
4	Gate (G)		
5~8	Drain (D)		

4. Limiting Values

Symbol	Parameter		Rating	Unit
V_{DS}	Drain-Source Voltage		- 30	V
V_{GS}	Gate-Source Voltage		± 25	
I_{DS}	Drain-Source Current	T_C = 25 ℃, V_{GS} = - 10 V	- 54	A
		T_C = 100 ℃, V_{GS} = - 10 V	- 35	
I_{DM}[Note1]	Pulsed Drain-Source Current	T_C = 25 ℃, V_{GS} = - 10 V	- 108	A
I_S	Diode Forward Current	T_C = 25 ℃, V_{GS} = 0 V	- 54	
E_{AS}	Single Pulsed Avalanche Energy	L = 1.0 mH	288	mJ
P_{tot}	Total Power Dissipation	T_C = 25 ℃	41	W
$R_{\theta JA}$[Note2]	Thermal Resistance- Junction to Ambient		60	℃ / W
$R_{\theta JC}$	Thermal Resistance- Junction to Case		3	
T_{stg}	Storage Temperature		- 55 ~ 150	℃
T_J	Junction Temperature		150	

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5. Electrical Characteristics (T_A = 25 °C Unless Otherwise Noted)

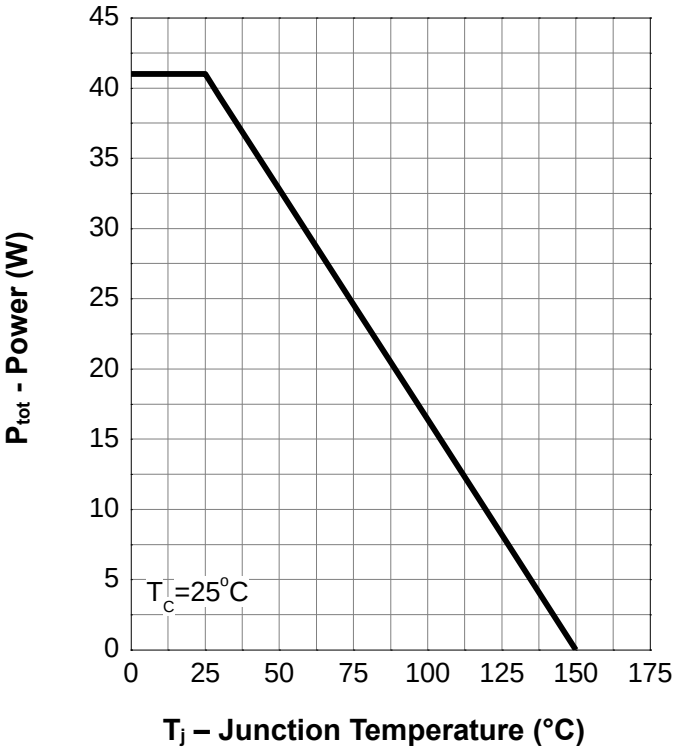
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_{DS} = - 250 μA	- 30	-	-	V
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{DS} = V_{GS}, I_{DS} = - 250 μA	- 1	-	- 3	
I_{DSS}	Drain-Source Leakage Current	V_{DS} = - 24 V, V_{GS} = 0 V	-	-	- 1	μA
		V_{DS} = - 24 V, V_{GS} = 0 V, T_J = 85 ℃	-	-	- 30	
I_{GSS}	Gate-Source Leakage Current	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 10	μA
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS} = - 10 V, I_{DS} = - 11.5 A	-	6	7.5	mΩ
		V_{GS} = - 4.5 V, I_{DS} = - 8.5 A	-	9	11.5	
Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_{SD} = - 1 A, V_{GS} = 0 V	-	- 0.7	- 1.2	V
t_{rr}[Note3]	Reverse Recovery Time	I_{SD} = - 11.5 A, V_{GS} = 0 V dI_{SD}/dt = 100 A/μs	-	57	-	nS
Q_{rr}[Note3]	Reverse Recovery Charge		-	18	-	nC
Dynamic Characteristics[Note3]						
C_{iss}	Input Capacitance	V_{GS} = 0 V, V_{DS} = - 15 V Frequency = 1 MHz	-	5963	-	pF
C_{oss}	Output Capacitance		-	723	-	
C_{rss}	Reverse Transfer Capacitance		-	674	-	
t_d(on)	Turn-on Delay Time	V_{DS} = - 15 V, V_{GEN} = - 10 V, R_G = 2.4 Ω, R_L = 1.3 Ω, I_{DS} = - 11.5 A	-	20	-	nS
t_r	Turn-on Rise Time		-	62	-	
t_d(off)	Turn-off Delay Time		-	336	-	
t_f	Turn-off Fall Time		-	44	-	
Gate Charge Characteristics[Note3]						
Q_g	Total Gate Charge	V_{DS} = - 15 V, V_{GS} = - 10 V, I_{DS} = - 11.5 A	-	126	-	nC
Q_{gs}	Gate-Source Charge		-	23	-	
Q_{gd}	Gate-Drain Charge		-	19	-	

Note 1：Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
Note 2：Surface Mounted on 1 in^2 pad area, t ≤ 10 sec.
Note 3：Guaranteed by design, not subject to production testing.

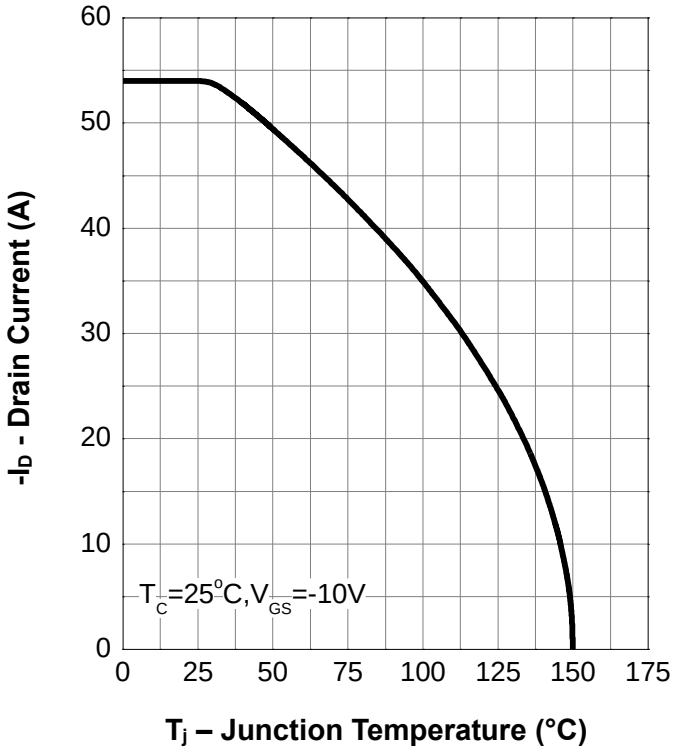
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6. Typical Characteristics

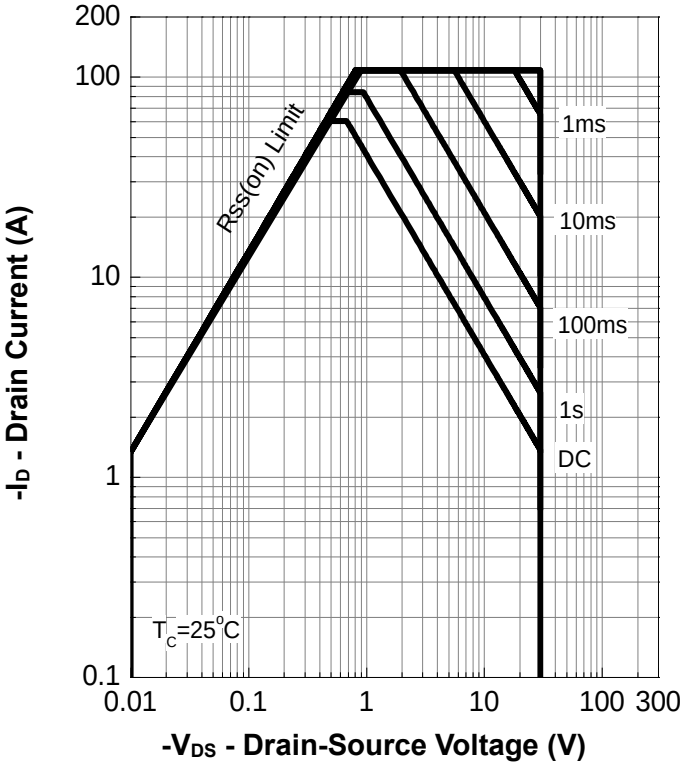
Power Capability



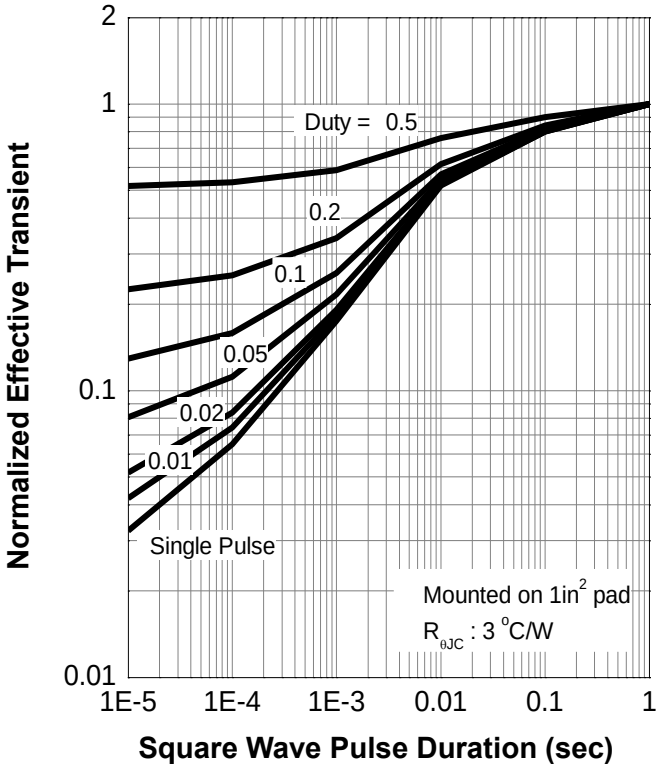
Current Capability



Safe Operating Area



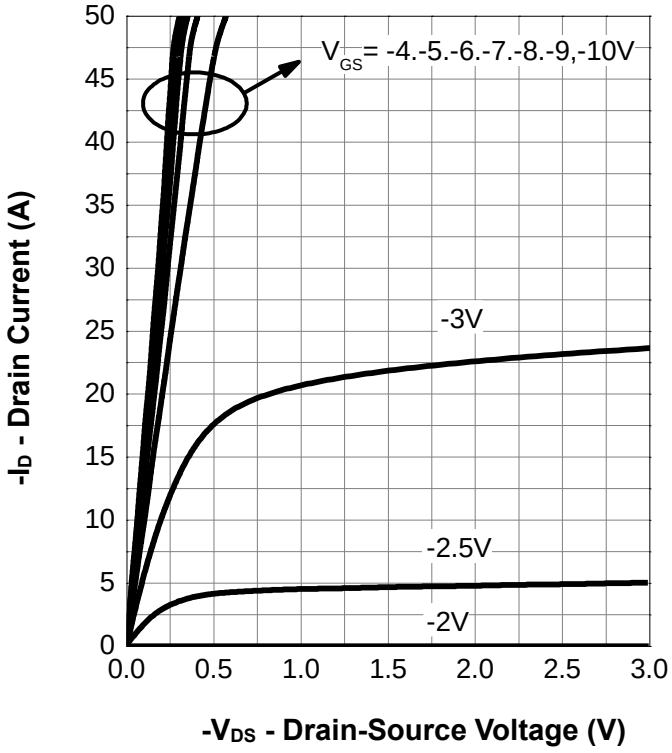
Transient Thermal Impedance



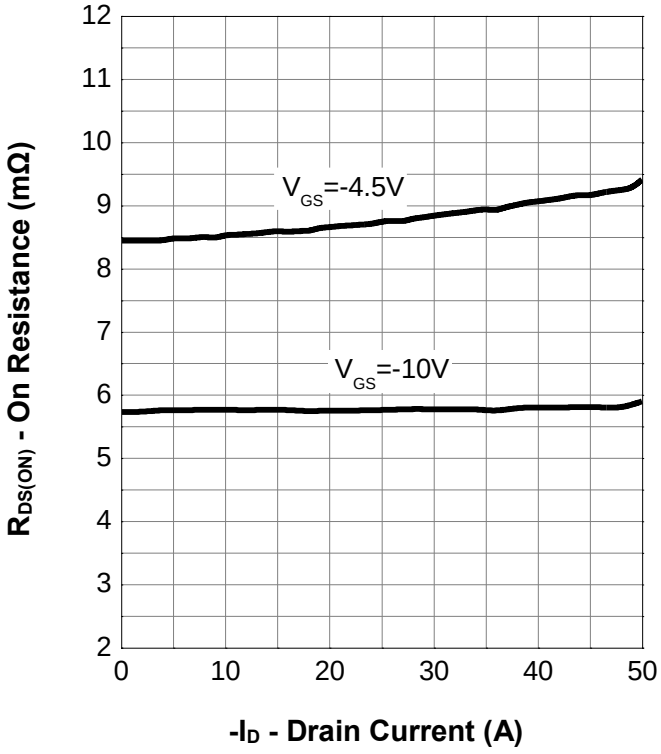
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6. Typical Characteristics (cont.)

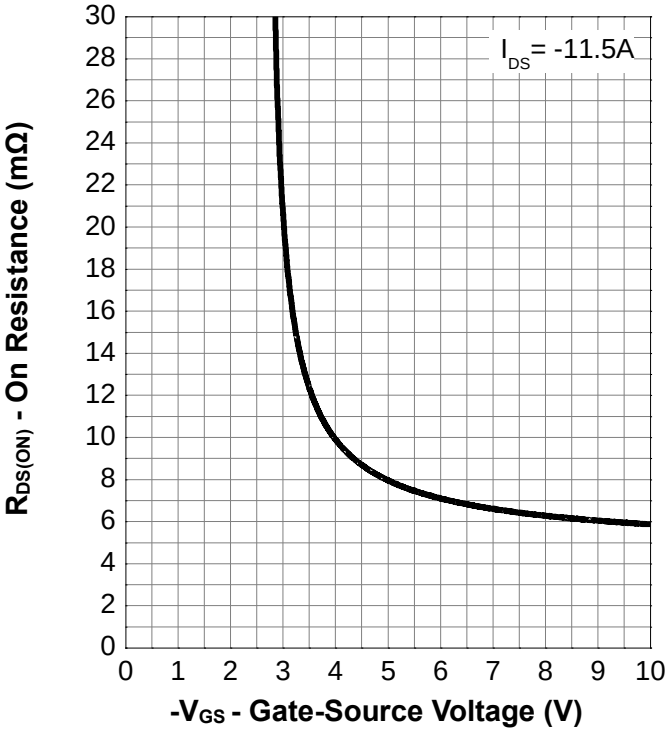
Output Characteristics



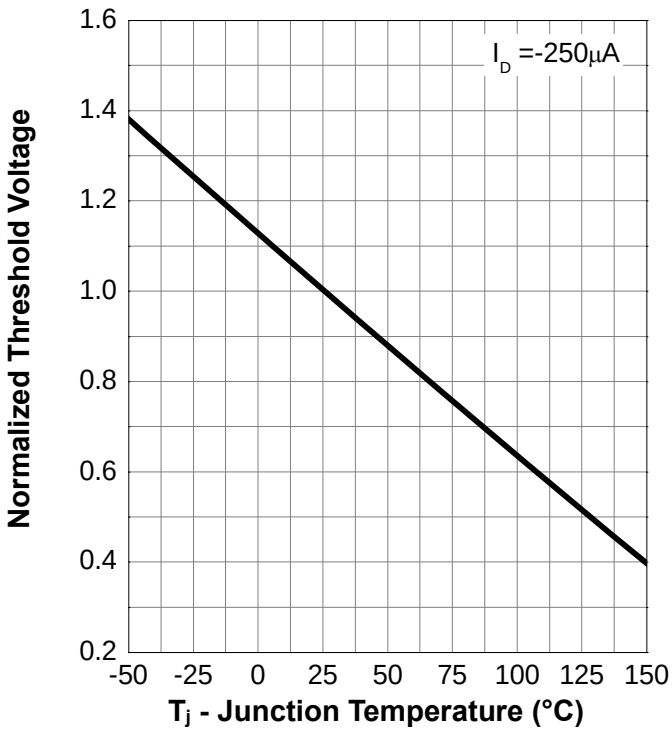
On Resistance



Transfer Characteristics



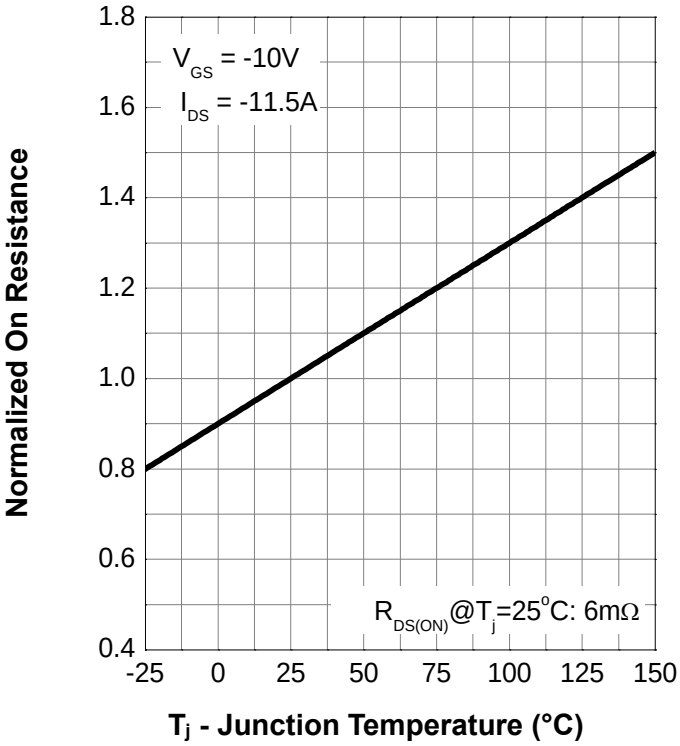
Normalized Threshold Voltage



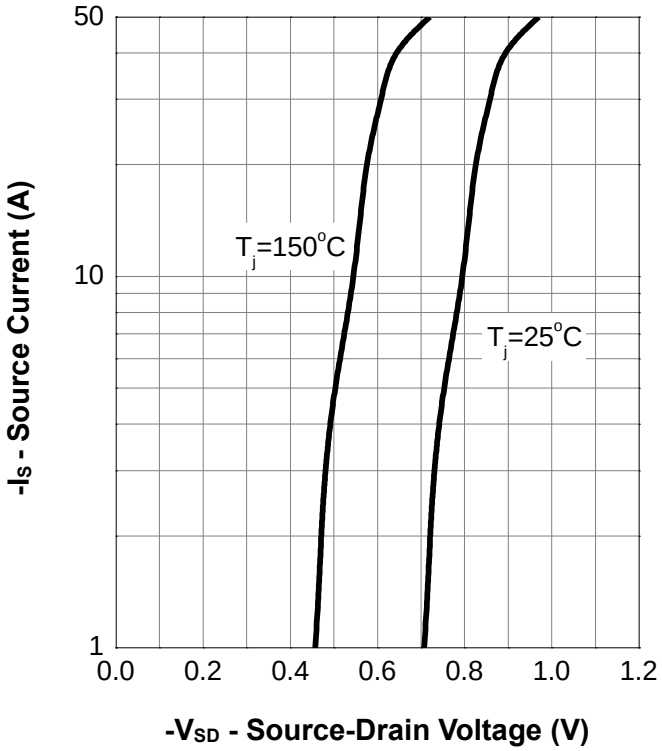
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6. Typical Characteristics (cont.)

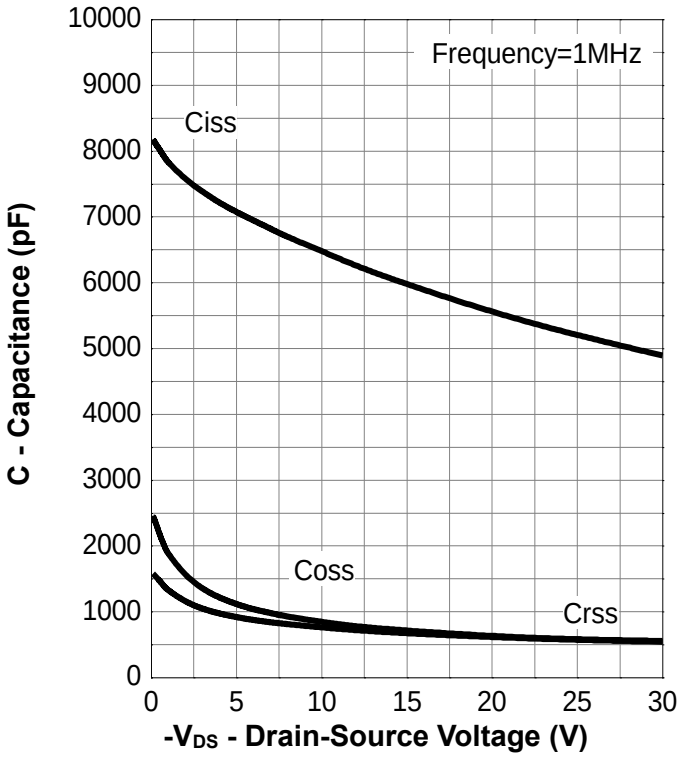
Normalized On Resistance



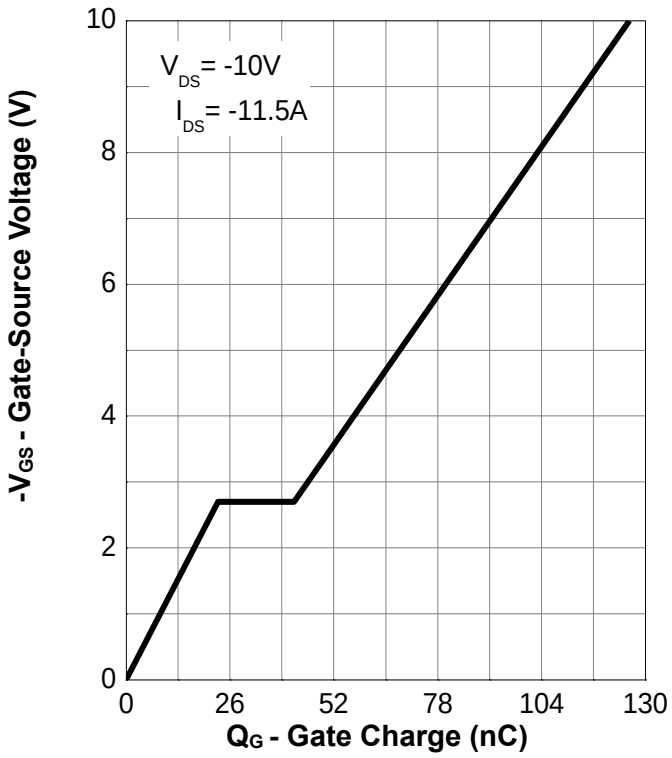
Diode Forward Current



Capacitance



Gate Charge



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